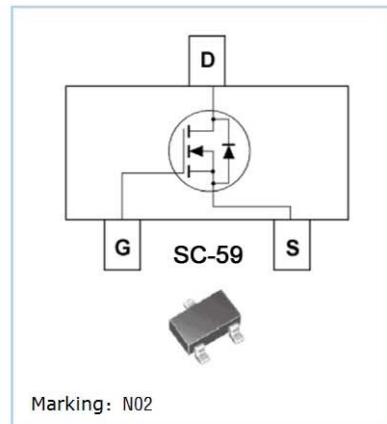


Feature

- 20V/3.6A, R_{D(S)}(ON) = 80m Ω (MAX) @V_{GS} = 4.5V.
R_{D(S)}(ON) = 90m Ω (MAX) @V_{GS} = 2.5V.
- Super High dense cell design for extremely low R_{D(S)}(ON).
- Reliable and Rugged.
- SC-59 for Surface Mount Package.


Applications

- Power Management
Portable Equipment and Battery Powered Systems.

Absolute Maximum Ratings

T_A=25°C Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±8	V
Drain Current-Continuous	I _D	3.6	A

Electrical Characteristics

T_A=25°C Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BVDSS	V _{GS} =0V, ID=250 μA	20	-	-	V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =12V, V _{GS} =0V	-	-	1	μA
Gate Body Leakage Current, Forward	IGSSF	V _{GS} =8V, V _{DS} =0V	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	V _{GS} =-8V, V _{DS} =0V	-	-	-100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , ID=250μA	0.4	-	1.3	V
Static Drain-source	R _{D(S)} (ON)	V _{GS} = 4.5V, ID = 3.6A	-	70	80	mΩ
On-Resistance		V _{GS} = 2.5V, ID = 3.1A	-	75	90	mΩ
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} = 0V, IS=0.94A			1.2	V

Typical Characteristics

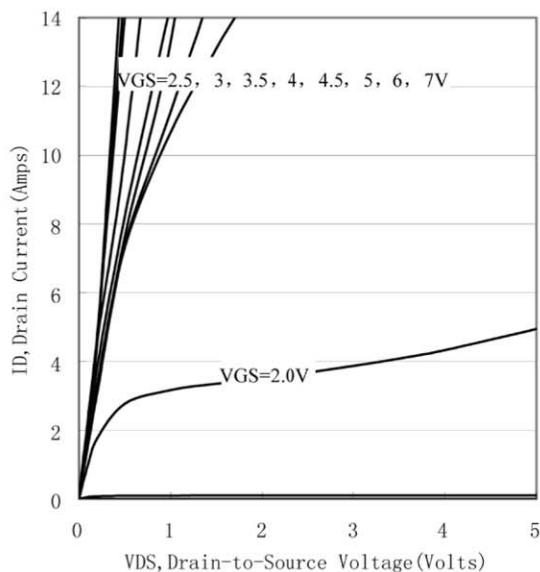


Figure 1. Output Characteristics

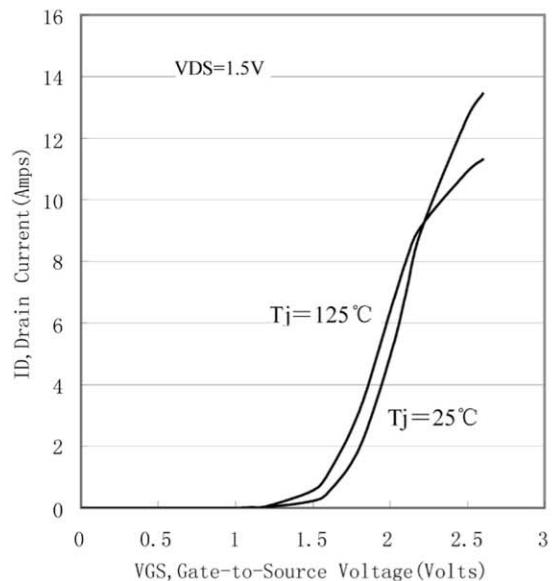


Figure 2. Transfer Characteristics

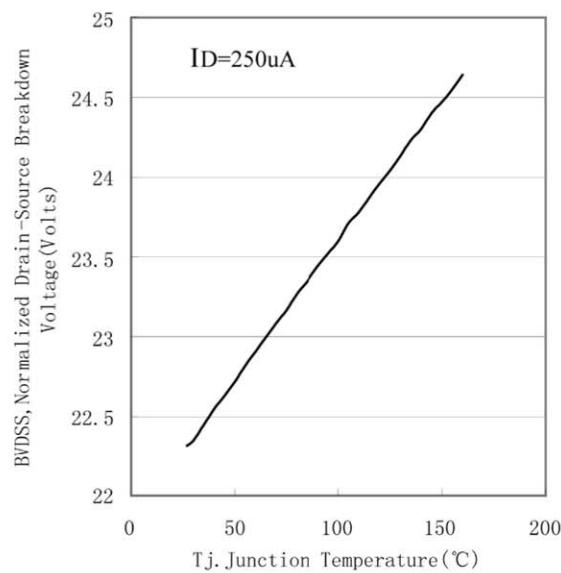


Figure 3. Breakdown Voltage Variation with Temperature

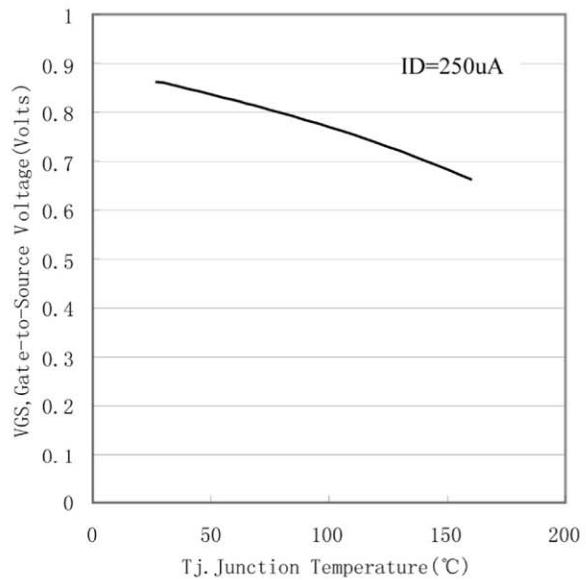


Figure 4. Gate Threshold Variation with Temperature

Typical Characteristics

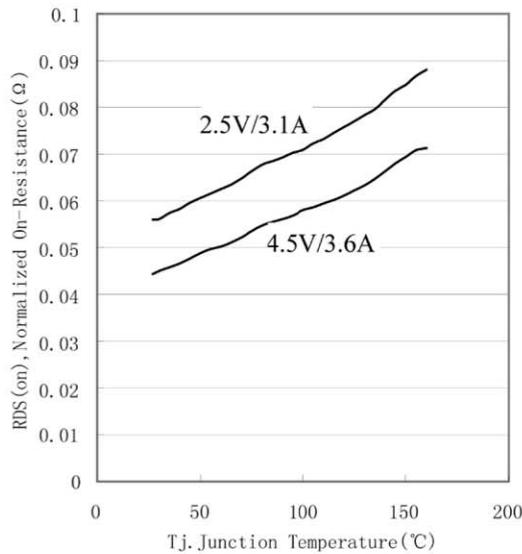


Figure 5. On-Resistance Variation with Temperature

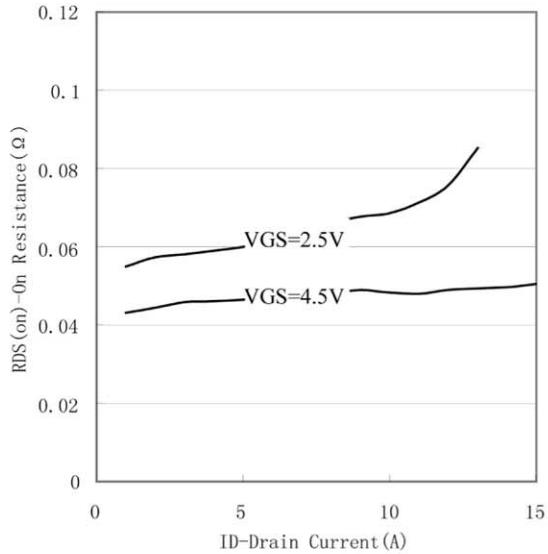


Figure 6. On-Resistance vs. Drain Current

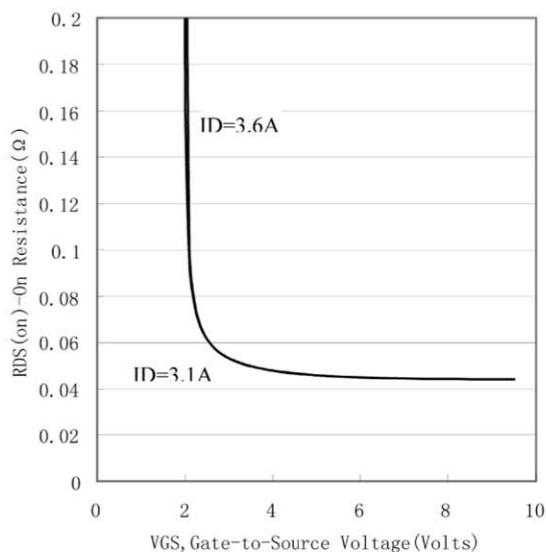


Figure 7. On-Resistance vs. Gate-to-Source Voltage

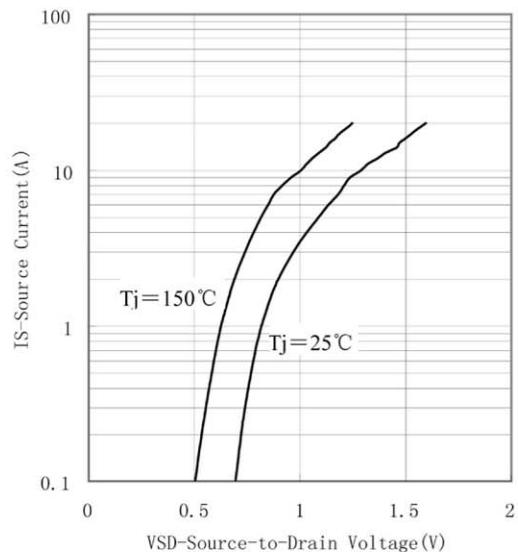


Figure 8. Source-Drain Diode Forward Voltage